L Number	Hits	Search Text	DB	Time stamp
1	0	438/257,263, 264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 14:34
2	588	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 14:34
3	7	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 14:36
4	3	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:15
5	1	6136652.pn. and (oxide same "40")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:12
6	1	6136652.pn. and (oxide same "40" adj angstroms)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:12
7	0	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228 and ((p adj channel) or p-channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:16
8	3	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228 and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:17
9	1	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228 and (erase same volt$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:21
10	1	6136652.pn. and (erase same volt$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:23
11	1	6136652.pn. and (erase same volt$3 same (floating adj gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:30
12	0	6245613.pn. and (erase same volt$3 same (floating adj gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:30
13	0	6246089.pn. and (erase same volt$3 same (floating adj gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:31
-	790596	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/26 14:01
-	1819	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/10 14:38

-	53	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/11 19:01
-	791060	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/10 17:10
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 adj micron adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/11 19:02
-	43	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 or quarter adj micron adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 11:11
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.25 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/11 19:04
-	15	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.25 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:35
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.25 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/11 19:28
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.18 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:32
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.18) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:33
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.18) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:33
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.15) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:33
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.1) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:33
-	0	(.1) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:34
-	0	(.18) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:34
-	0	(.25) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:34
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.25) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:35

-	15	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.25 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:36
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.25) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:36
-	43	438/257.CCLS. AND (memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 or quarter adj micron adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/13 16:25
-	43	257/315,316.CCLS. AND 438/257.CCLS. AND (memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 or quarter adj micron adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/13 16:26
-	48	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate and oxide adj layer with "50" adj angstroms and .25 or quarter adj micron adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 12:16
-	1797	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate and oxide adj layer and "50" adj angstroms and .25 or quarter adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 12:08
-	0	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj angstroms) and (.25 or quarter adj micron adj gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 12:22
-	57	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj angstroms))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 18:04
-	0	257/315,316.ccls and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj angstroms))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 16:38
-	9	438/264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj angstroms))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 18:01
-	0	438/264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("23" adj angstroms))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/29 16:04
-	0	6515328.pn. and (p adj channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:41
-	0	6515328.pn. and (p adj channel or positiv$3 adj dop$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:43
-	0	6515328.pn. and ((p adj channel) or (positiv$3 adj dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:44
-	0	5852311.pn. and ((p adj channel) or (positiv$3 adj dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:45

-	0	5869370.pn. and ((p adj channel) or (positiv$3 adj dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:46
-	0	6515328.pn. and ((p adj channel) or (positiv$3 adj dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:46
-	0	6383939.pn. and ((p adj channel) or (positiv$3 adj dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:47
-	0	6316316.pn. and ((p adj channel) or (positiv$3 adj dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:47
-	1	6456535.pn. and ((p adj channel) or (positiv$3 adj dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:48
-	0	6261906.pn. and ((p adj channel) or (positiv$3 adj dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:48
-	0	6261906.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:49
-	0	5852311.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:49
-	0	5869370.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:50
-	0	5852311.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:50
-	0	5869370.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:50
-	0	6515328.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:51
-	0	6316316.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:51
-	1	6456535.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:51
-	0	6261906.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:55
-	0	6372651.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:56
-	0	6383939.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:56
-	0	6515328.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:57

-	0	6316316.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:57
-	1	6456535.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:57
-	0	6249819.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:58
-	0	20030201477.pn. and ((p adj channel) or (positiv$3 same dop$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 17:58
-	0	438/264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj angstroms)) and ((p adj channel) or (p-channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 18:02
-	18	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj angstroms)) and ((p-channel) or (p adj channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 13:44
-	303	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((p-channel) or (p adj channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13 18:10
-	3	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 14:47
-	1	5408115.pn. and ((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 14:18
-	13	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("30" adj angstroms)) and ((p-channel) or (p adj channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 14:53
-	13	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("23" adj angstroms)) and ((p-channel) or (p adj channel))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 14:54
-	0	6515328.pn. and (p-channel or p adj channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/26 14:02
-	0	6372651.pn. and (p-channel or p adj channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/26 14:03
-	0	6383939.pn. and (p-channel or p adj channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/26 14:04
-	0	6383939.pn. and (p-channel or p adj channel or p channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/26 14:04

-	0	438/257,263, 264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 14:35
-	0	438/257,263, 264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (oxide adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/29 16:05
-	0	438/257,263, 264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 14:33